

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030242US1	Application No. 10/715,400
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Dureseti CHIDAMBARRAO			
		Filing Date 11/19/2003	Group 2813		

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EXAMINER <i>JAM</i>		DATE CONSIDERED <i>9/20/06</i>		
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